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January 2014

FQD12N20L

N-Channel QFET® MOSFET

200 V, 9.0 A, 280 mΩ

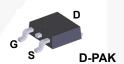
Description

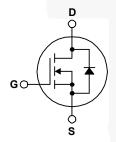
This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state

Low Gate Charge (Typ. 16 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 17 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- 9.0 A, 200 V, $R_{DS(on)}$ = 280 m Ω (Max.) @ V_{GS} = 10 V, $I_D = 4.5 A$





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQD12N20LTM	Unit	
V_{DSS}	Drain-Source Voltage		200	V	
I _D	Drain Current - Continuous (T _C = 25°C)		9.0	Α	
	- Continuous (T _C = 100°C)		5.7	Α	
I _{DM}	Drain Current - Pulsed	(Note 1)	36	Α	
V _{GSS}	Gate-Source Voltage		± 20	V	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		210	mJ	
I _{AR}	Avalanche Current (Note 1)		9.0	Α	
E _{AR}	Repetitive Avalanche Energy (Note 1)		5.5	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		5.5	V/ns	
P _D	Power Dissipation (T _A = 25°C) *		2.5	W	
	Power Dissipation (T _C = 25°C) - Derate above 25°C		55	W	
			0.44	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
T _L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C	
· L			300	C	

Thermal Characteristics

R _{0JC} Thermal Resistance, Junction to Case, Max. 2.27	
Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max. 110	°C/W
R _{0JA} Thermal Resistance, Junction to Ambient (*1 in² Pad of 2-oz Copper), Max. 50	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQD12N20LTM	FQD12N20L	DPAK	Tape and Reel	330 mm	16 mm	2500 units

Electrical Characteristics

T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	200			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.14		V/°C
I _{DSS}	V _{DS} = 200 V, V _{GS} = 0 V			1	μΑ	
Zero Gate Voltage Drain Current		V _{DS} = 160 V, T _C = 125°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
	racteristics					
	Cata Throphold Valtage	V = V Ι- = 250 μΔ	1.0		2.0	1/
V _{GS(th)}	Gate Threshold Voltage Static Drain-Source On-Resistance	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$ $V_{GS} = 10 \text{V}, I_D = 4.5 \text{A}$ $V_{CS} = 5 \text{V}, I_D = 4.5 \text{A}$	1.0	 0.22 0.25	2.0 0.28 0.32	V Ω
		50 00 5				-
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 4.5 A V _{GS} = 5 V, I _D = 4.5 A		0.22 0.25	0.28 0.32	Ω
R _{DS(on)}	Static Drain-Source On-Resistance Forward Transconductance	$V_{GS} = 10 \text{ V}, I_D = 4.5 \text{ A}$ $V_{GS} = 5 \text{ V}, I_D = 4.5 \text{ A}$ $V_{DS} = 30 \text{ V}, I_D = 4.5 \text{ A}$		0.22 0.25	0.28 0.32	Ω
R _{DS(on)} 9 _{FS} Dynam	Static Drain-Source On-Resistance Forward Transconductance ic Characteristics	V _{GS} = 10 V, I _D = 4.5 A V _{GS} = 5 V, I _D = 4.5 A		0.22 0.25 11.6	0.28 0.32	Ω S

Switching Characteristics

	•						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 100 V, I _D = 11.6 A,		-	15	40	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$			190	390	ns
t _{d(off)}	Turn-Off Delay Time	· · · ·		-	60	130	ns
t _f	Turn-Off Fall Time		(Note 4)	-	120	250	ns
Q_g	Total Gate Charge	V _{DS} = 160 V, I _D = 11.6 A,			16	21	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 5 V		-	2.8		nC
Q_{gd}	Gate-Drain Charge		(Note 4)	-	7.6		nC

Drain-Source Diode Characteristics and Maximum Ratings

IS	Maximum Continuous Drain-Source Diode Forward Current				9.0	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				36	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 9.0 A			1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 11.6 A,		128		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		0.56		μС

Notes. In Repetitive rating: pulse width limited by maximum junction temperature. 2. L = 3.9 mH, I $_{AS}$ = 9.0 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C. 3. I $_{SD}$ \leq 11.6 A, di/dt \leq 300 A/ μ s, V $_{DD}$ \leq BV $_{DSS}$, starting T $_{J}$ = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

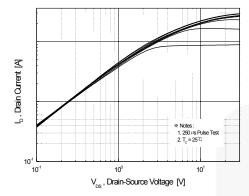
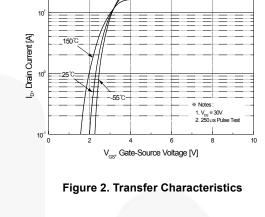


Figure 1. On-Region Characteristics



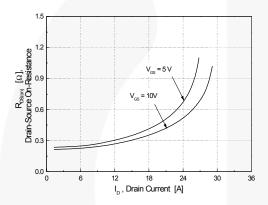


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

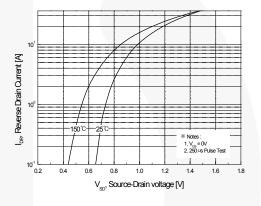


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

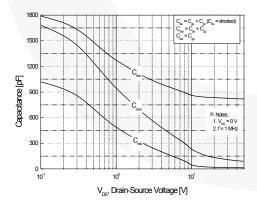


Figure 5. Capacitance Characteristics

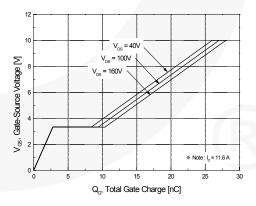


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

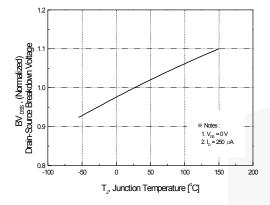


Figure 7. Breakdown Voltage Variation vs. Temperature

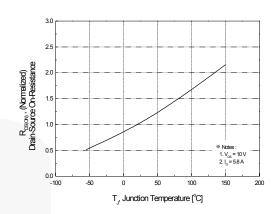


Figure 8. On-Resistance Variation vs. Temperature

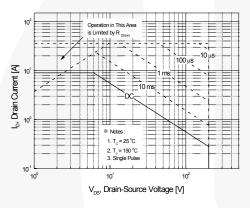


Figure 9. Maximum Safe Operating Area

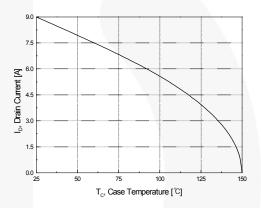


Figure 10. Maximum Drain Current vs. Case Temperature

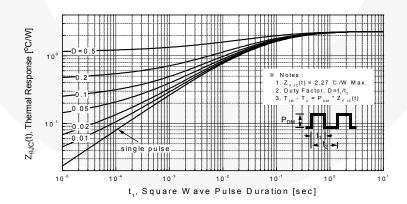


Figure 11. Transient Thermal Response Curve

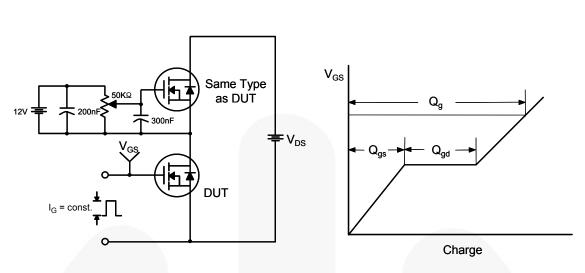


Figure 12. Gate Charge Test Circuit & Waveform

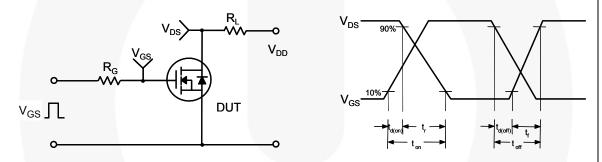


Figure 13. Resistive Switching Test Circuit & Waveforms

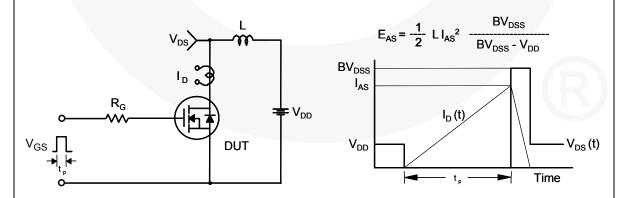
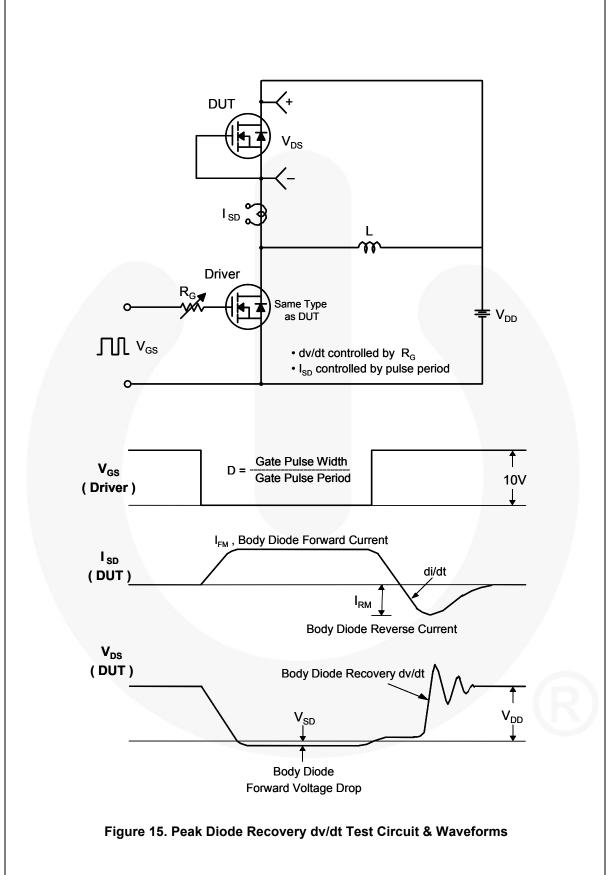


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions -5.55 MIN→ 1.27 6.22 5.97 6.50 MIN -1.02 MAX Ċ 2 (0.59)0.89 2.29 .25 2.28 ⊕ 0.25 A A C 4.57 LAND PATTERN RECOMMENDATION B 2.39 SFF 2.18 4.32 MIN NOTE D 0.58 0.45 5.21 MIN 10.41 9.40 SFF DFTAIL A ○ 0.10 B 0.51 GAGE PLANE NOTES: UNLESS OTHERWISE SPECIFIED THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA. ALL DIMENSIONS ARE IN MILLIMETERS. 10 (1.54)DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009. SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION. PRESENCE OF TRIMMED CENTER LEAD .78 .40 0.127 MAX IS OPTIONAL. DIMENSIONS ARE EXCLUSSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS. SEATING PLANE

Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

(2.90)

DETAIL

(ROTATED -90°) SCALE: 12X

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LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD

DRAWING NUMBER AND REVISION: MKT-T0252A03REV9.

T0228P991X239-3N.

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Preliminary First Production		Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.			
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